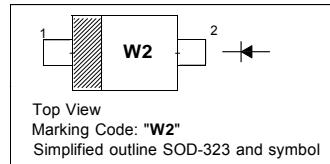


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-repetitive Peak Forward Surge Current at $t = 1 \text{ s}$ at $t = 1 \text{ ms}$ at $t = 1 \mu\text{s}$	I_{FSM}	0.5 1 4	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$	I_R	30 1 30 50	nA μA μA μA
Diode Capacitance at $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_{tot}	1.5	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$, $I_R = 1 \text{ mA}$, $R_L = 100 \Omega$	t_{rr}	4	ns

Typical Characteristics

Fig 1. Power Dissipation vs. Temperature

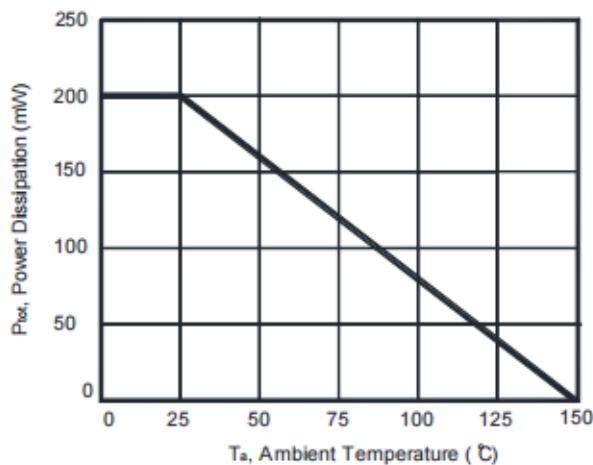


Fig 2. Total Capacitance vs. Reverse Voltage

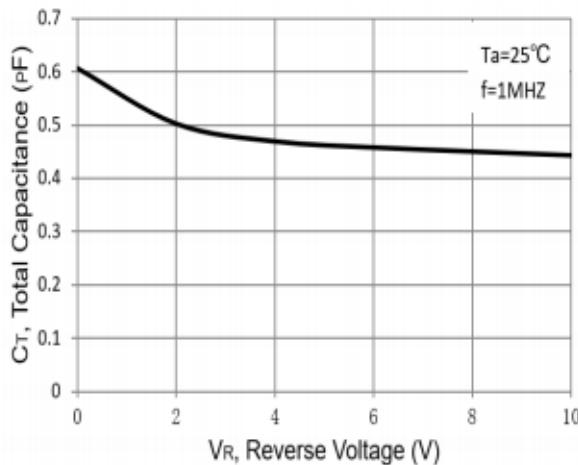


Fig 3. Reverse Current vs. Reverse Voltage

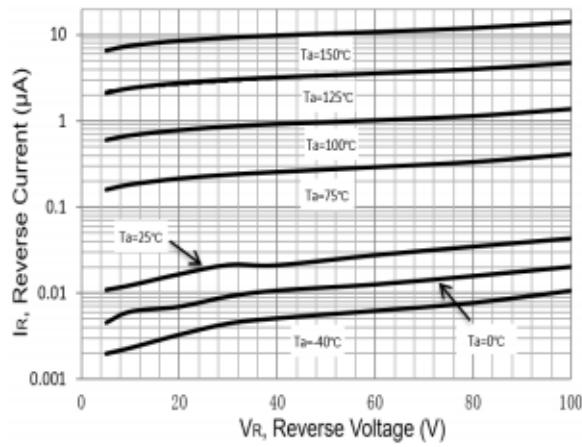


Fig 4. Forward Characteristics

